### **Digital Transistors (BRT)** R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$

### **PNP Transistors with Monolithic Bias Resistor Network**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector–Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

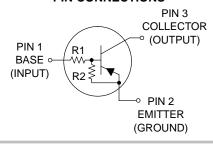
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



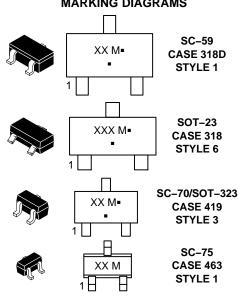
### ON Semiconductor®

www.onsemi.com

### **PIN CONNECTIONS**



### **MARKING DIAGRAMS**



XXX Specific Device Code Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

SOT-723

CASE 631AA

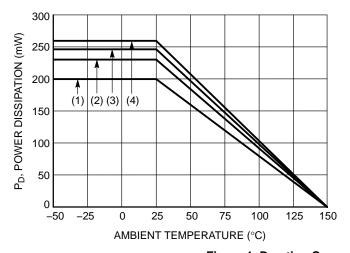
STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2136T1G	6N	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2136LT1G, NSVMMUN2136LT1G*	ACG	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5136T1G, NSVMUN5136T1G*	6N	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA115EET1G, NSVDTA115EET1G*	6N	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA115EM3T5G	6N	SOT-723 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-723; Minimum Pad

Figure 1. Derating Curve

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2136)	•		•	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2136L)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5136)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTA115EE)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	200 300 1.6 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTA115EM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1)	P <sub>D</sub>	260 600 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 1) (Note 2)	$R_{ heta JA}$	4.8 480 205	°C/W
Junction and Storage Temperature Range	(11010 2)	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

<sup>1.</sup> FR-4 @ Minimum Pad.

<sup>2.</sup> FR-4 @ 1.0 x 1.0 Inch Pad.

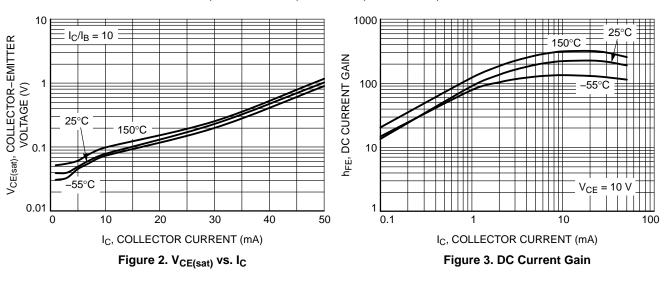
Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25$ °C, unless otherwise noted)

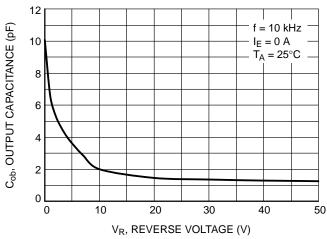
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•	•	
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	_	_	500	nAdc
Emitter–Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	0.05	mAdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	50	_	_	Vdc
Collector–Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	_	-	Vdc
ON CHARACTERISTICS	<u>.</u>				
DC Current Gain (Note 3) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	150	_	
Collector–Emitter Saturation Voltage (Note 3) $(I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA})$	V <sub>CE(sat)</sub>	_	_	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	_	1.2	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_{C} = 1.0 \text{ mA})$	V <sub>i(on)</sub>	3.0	1.6	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 5.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	-	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	_	-	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

## TYPICAL CHARACTERISTICS MUN2136, MMUN2136L, MUN5136, DTA115EE, DTA115EM3





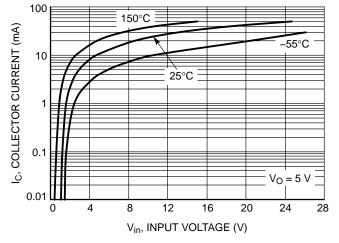


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

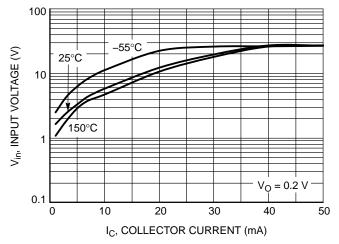


Figure 6. Input Voltage vs. Output Current

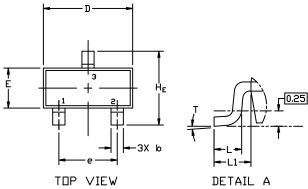




**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	ETERS		INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

# GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **STYLES ON PAGE 2**

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2		

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## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2		

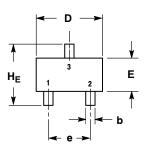
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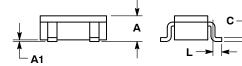




SC-59 CASE 318D-04 ISSUE H

**DATE 28 JUN 2012** 





### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code М

= Pb-Free Package\*

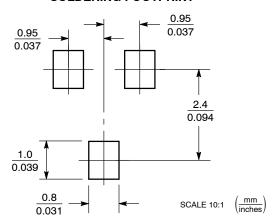
(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. CATHODE	PIN 1. ANODE
2. N.C.	2. CATHODE	2. CATHODE
3. ANODE	3. ANODE	3. ANODE/CATHODE

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DESCRIPTION:	SC-59		PAGE 1 OF 1		

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SC-70 (SOT-323) **CASE 419** ISSUE R

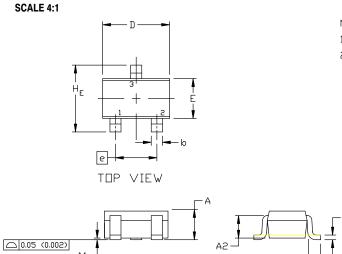
END VIEW

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M:	ILLIMETE	RS		INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF	-		0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



### **GENERIC MARKING DIAGRAM**

SIDE VIEW

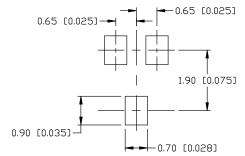


= Specific Device Code XX

М = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

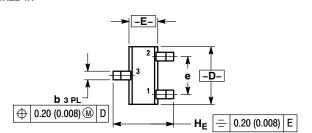
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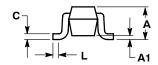




SC-75/SOT-416 **CASE 463** ISSUE G

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. COLLECTOR 3. CATHODE STYLE 4: STYLE 5: PIN 1. CATHODE 2. CATHODE PIN 1. GATE 2. SOURCE

3. DRAIN

### **GENERIC MARKING DIAGRAM\***

3. ANODE



XX = Specific Device Code Μ = Date Code

= Pb-Free Package

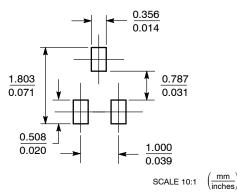
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

### NOTES

1. DIMENSIONING AND TOLERANCING PER ANSI Y14,5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	;
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC			C	0.04 BSC	
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

### RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

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MILLIMETERS

 $N\square M$ .

0.50



### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

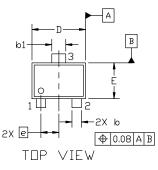
**DATE 24 JAN 2024** 

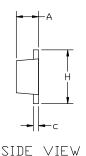
MAX.

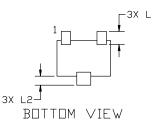
0.55

### NOTES:

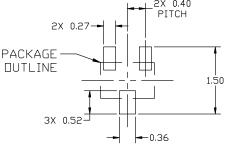
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
Е	0.75	0.80	0.85	
е	0.40 BSC			
Н	1.15	1.20	1.25	
L		0.29 REF	-	
L2	0.15	0.20	0.25	
2X 0.40 PITCH				



DIM

Α

MIN.

0.45

### RECOMMENDED MOUNTING FUUTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
<ol><li>EMITTER</li></ol>	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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